



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

**SOD-123 封装二极管/SOD-123 Plastic-Encapsulate Diodes**

**B5817W/B5818W/B5819W (SCHOTTKY DIODES)**

**特点/Features :**

正向导通电压低 ;

**用途/Applications :**

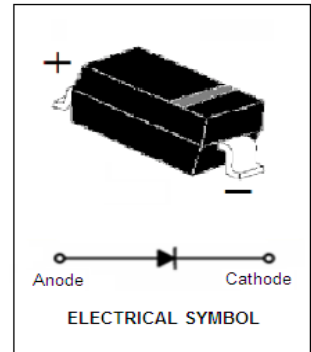
低压、高频等保护电路。

**印章/ Marking:**

B5817W: **SJ**

B5818W: **SK**

B5819W: **SL**



**极限参数/Absolute maximum ratings(Ta=25°C)**

Parameter	Symbol	B5817W	B5818W	B5819W	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	20	30	40	
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$				
Working Peak	$V_{RWM}$	20	30	40	V
DC Blocking Voltage	$V_R$				
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average rectified output current	$I_O$		1		A
Peak Forward Surge Current (@t≤8.3mS)	$I_{FSM}$		9		A
Repetitive Peak Forward Current	$I_{FRM}$		1.5		A
Power Dissipation	$P_d$		500		mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$		200		°C/mW
Storage Temperature	Tstg		-55~150		°C

**电性能参数/Electrical characteristics (Ta=25°C)**

参数/Parameter	符号	测试条件	最小值	典型值	最大值	单位
Reverse Breakdown Voltage B5817W B5818W B5819W	$V_{(BR)}$	$I_R=1mA$	20 30 40			V
Forward Voltage	$V_F$	$I_F=1A$ B5817W B5818W B5819W			0.45 0.55 0.6	V
		$I_F=3A$ B5817W B5818W B5819W			0.75 0.875 0.9	V
Reverse voltage leakage current B5817W B5818W B5819W	$I_R$	$V_R=20V$ $V_R=30V$ $V_R=40V$			1	mA
Diode Capacitance	$C_D$	$V_R=4V, f=1.0MHz$			120	pF



### 典型特性曲线图/Typical Characteristics

